



## Program

1:00 PM	1:05 PM	Talk 1	Introduction to IWMSE	Session Chair (A.Hinz/A.Žukauskaitė)	Kyoto Fusioneering/ Fraunhofer FEP
1:05 PM	1:45 PM	Talk 2	Device and Process Technology for GaN Power Transistors: Perspective of Automotive Applications	0	Robert Bosch GmbH, Reutlingen, Germany
1:45 PM	2:05 PM	Talk 3	Growth and Study of Epitaxial Metal Nitride Thin Films using Reactive Magnetron Sputtering	Dr. Mukul Gupta	UGC-DAE Consortium for Scientific Research, Indore, India
2:05 PM	2:25 PM	Talk 4	Ferroelectricity in undoped AlN enabled by sputter-epitaxy	Georg Schönweger	Kiel University, Germany
2:25 PM	2:45 PM	Talk 5	Comparison of sputtered and MOVPE grown TiN	Dr. Florian Hörich	Otto-von-Guericke University Magdeburg, Germany
2:45 PM	3:00 PM	Coffee break			
3:00 PM	3:20 PM	Talk 6	Effects of W alloying on the electronic structure, phase stabili- ty and thermoelectric power factor in epitaxial CrN thin films	Niraj Singh	Uppsala University, Sweden
3:20 PM	3:40 PM	Talk 7	Scaled MSE of Group III Nitrides	Valentin Garbe	Fraunhofer FEP, Dresden, Germany
3:40 PM	4:00 PM	Talk 8	Sputter-epitaxy of Ternary Nitride MgTa2N3	Baptiste Julien	NREL, USA
4:00 PM	4:20 PM	Talk 9	Formation and avoidance of {111} oriented domains during the sputtering epitaxy growth of Ir(001) films on YSZ/Si(001)	Dr. Jürgen Weippert	Fraunhofer IAF, Freiburg, Germany
4:20 PM	4:40 PM	Talk 10	Structural and electrical properties of molybdenum thin films prepa- red by magnetron sputter epitaxy	Balasubramanian Sundarapandian	Fraunhofer IAF, Freiburg, Germany
4:40 PM	5:00 PM	Talk 11	Effect of substrate bias on the growth behavior of iridium on A-plane sapphire using radio frequency sputtering	Dr. Frank Meyer	Fraunhofer IWM, Freiburg, Germany
5:00 PM	5:20 PM	Talk 12	Closing remarks	Session Chair (A.Hinz/A.Žukauskaitė)	